

PBSS4160DPN

60 V, 1 A NPN/PNP low V_{CEsat} (BISS) transistor

Rev. 03 — 11 December 2009

Product data sheet

1. Product profile

1.1 General description

NPN/PNP low V_{CEsat} Breakthrough in Small Signal (BISS) transistor pair in a SOT457 (SC-74) Surface Mounted Device (SMD) plastic package.

1.2 Features

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- High collector current gain (h_{FE}) at high I_C
- High efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors

1.3 Applications

- Complementary MOSFET driver
- Half and full bridge motor drivers
- Dual low power switches (e.g. motors, fans)
- Automotive applications

1.4 Quick reference data

Table 1. Quick reference data

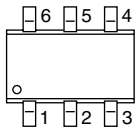
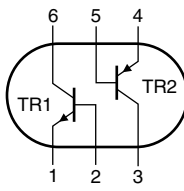
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
TR1 (NPN)						
V_{CEO}	collector-emitter voltage	open base	-	-	60	V
I_C	collector current (DC)		[1]	-	1	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	-	2	A
R_{CEsat}	collector-emitter saturation resistance	$I_C = 1$ A; $I_B = 100$ mA	[2]	200	250	m Ω
TR2 (PNP)						
V_{CEO}	collector-emitter voltage	open base	-	-	-60	V
I_C	collector current (DC)		[1]	-	-900	mA
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	-	-2	A
R_{CEsat}	collector-emitter saturation resistance	$I_C = -1$ A; $I_B = -100$ mA	[2]	250	330	m Ω

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

[2] Pulse test: $t_p \leq 300$ μ s; $\delta \leq 0.02$.

2. Pinning information

Table 2. Pinning

Pin	Description	Simplified outline	Symbol
1	emitter TR1		
2	base TR1		
3	collector TR2		
4	emitter TR2		
5	base TR2		
6	collector TR1		

sym019

3. Ordering information

Table 3. Ordering information

Type number	Package		Version
	Name	Description	
PBSS4160DPN	SC-74	plastic surface mounted package; 6 leads	SOT457

4. Marking

Table 4. Marking codes

Type number	Marking code
PBSS4160DPN	B4

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

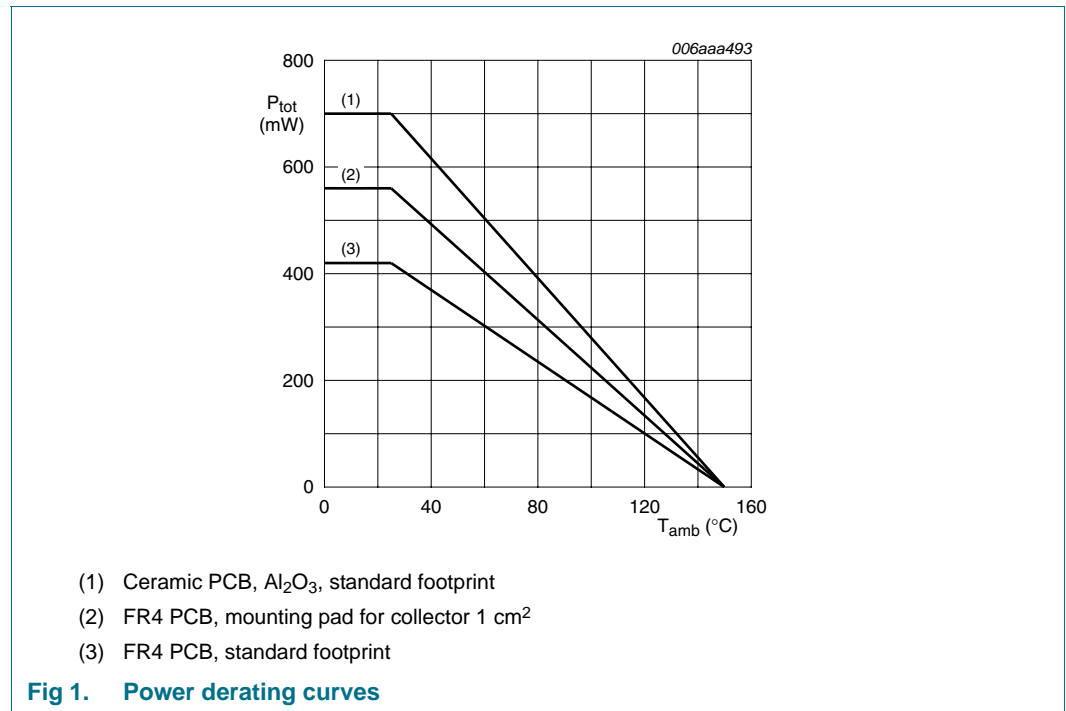
Symbol	Parameter	Conditions	Min	Max	Unit	
Per transistor unless otherwise specified; for the PNP transistor with negative polarity						
V_{CBO}	collector-base voltage	open emitter	-	80	V	
V_{CEO}	collector-emitter voltage	open base	-	60	V	
V_{EBO}	emitter-base voltage	open collector	-	5	V	
I_C	collector current (DC)	NPN	[1]	-	870	mA
			[2]	-	1	A
		PNP	[1]	-	770	mA
			[2]	-	900	mA
			[3]	-	1	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	2	A	
I_B	base current (DC)		-	300	mA	
I_{BM}	peak base current	single pulse; $t_p \leq 1$ ms	-	1	A	

Table 5. Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit	
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	[1]	-	290	mW
			[2]	-	370	mW
			[3]	-	450	mW
Per device						
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ °C}$	[1]	-	420	mW
			[2]	-	560	mW
			[3]	-	700	mW
T_j	junction temperature		-	150	°C	
T_{amb}	ambient temperature		-65	+150	°C	
T_{stg}	storage temperature		-65	+150	°C	

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.



6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	431	K/W
			[2]	-	-	338	K/W
			[3]	-	-	278	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	105	K/W	

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².
- [3] Device mounted on a ceramic PCB, Al₂O₃, standard footprint.

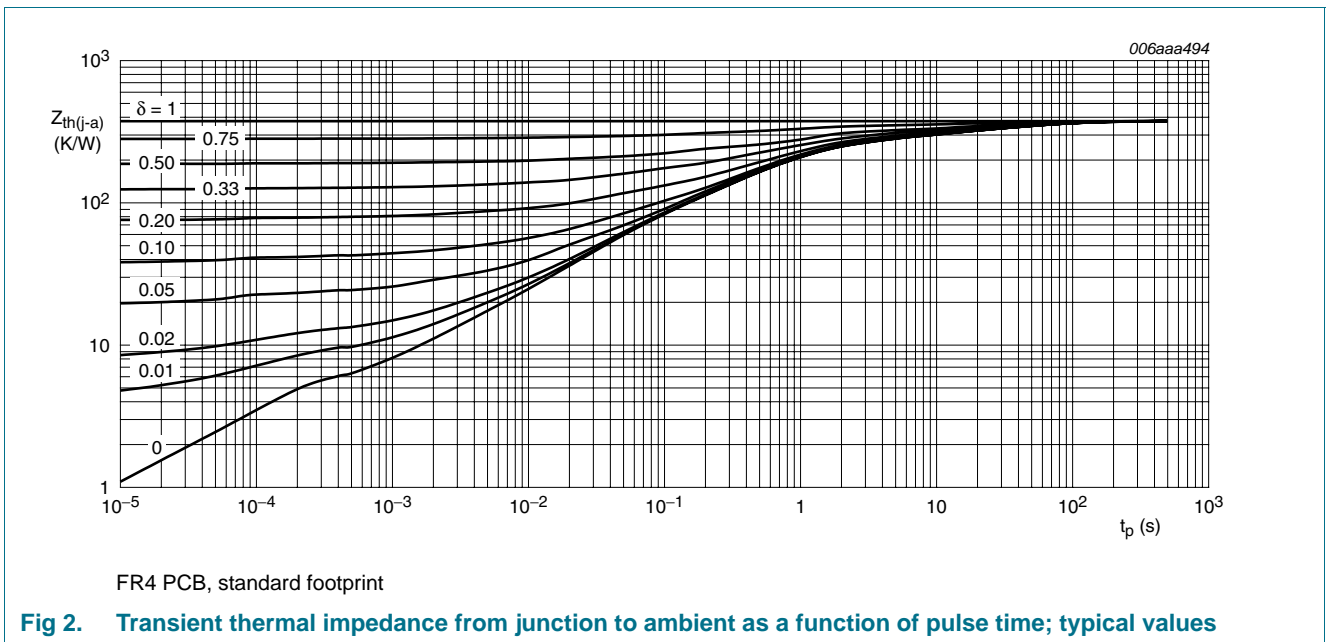


Fig 2. Transient thermal impedance from junction to ambient as a function of pulse time; typical values

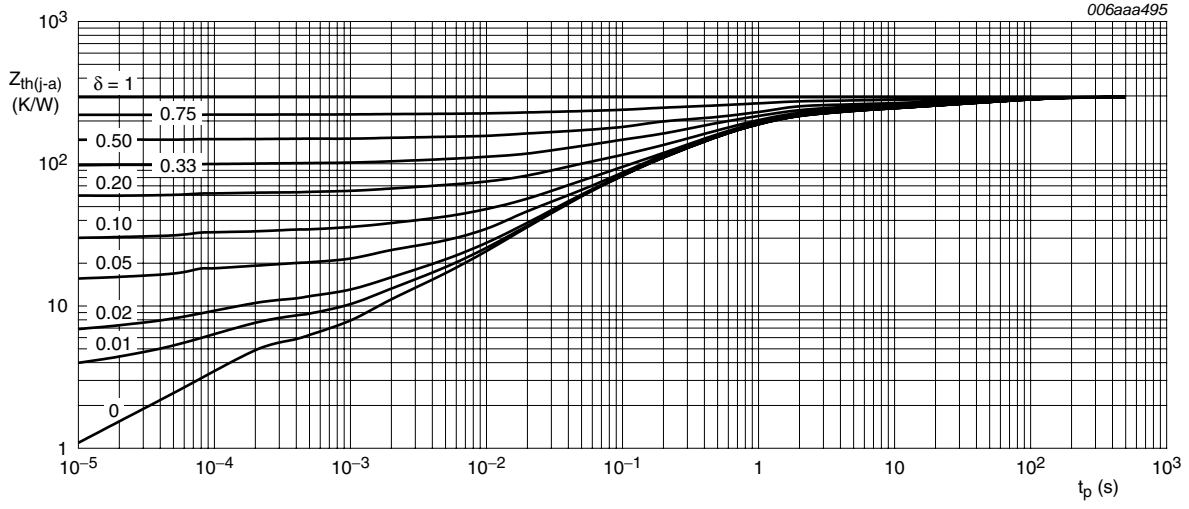


Fig 3. Transient thermal impedance from junction to ambient as a function of pulse time; typical values

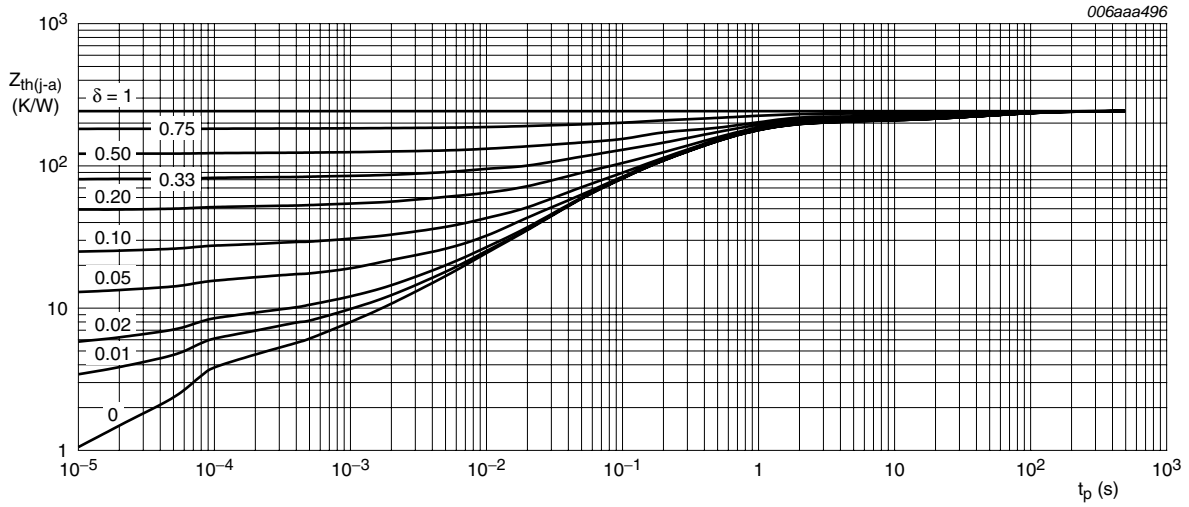


Fig 4. Transient thermal impedance from junction to ambient as a function of pulse time; typical values

7. Characteristics

Table 7. Characteristics

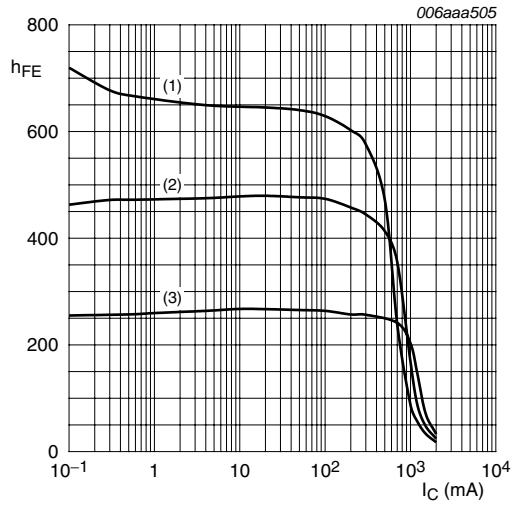
$T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
Per transistor unless otherwise specified; for the PNP transistor with negative polarity							
I_{CBO}	collector-base cut-off current	$V_{CB} = 60\text{ V}; I_E = 0\text{ A}$	-	-	100	nA	
		$V_{CB} = 60\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ }^{\circ}\text{C}$	-	-	50	μA	
I_{CES}	collector-emitter cut-off current	$V_{CE} = 60\text{ V}; V_{BE} = 0\text{ V}$	-	-	100	nA	
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0\text{ A}$	-	-	100	nA	
V_{BEsat}	base-emitter saturation voltage	$I_C = 1\text{ A}; I_B = 50\text{ mA}$	[1]	0.95	1.1	V	
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = 5\text{ V}; I_C = 1\text{ A}$	[1]	0.82	0.9	V	
TR1 (NPN)							
h_{FE}	DC current gain	$V_{CE} = 5\text{ V}; I_C = 1\text{ mA}$	250	500	-		
		$V_{CE} = 5\text{ V}; I_C = 500\text{ mA}$	[1]	200	420	-	
		$V_{CE} = 5\text{ V}; I_C = 1\text{ A}$	[1]	100	180	-	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 100\text{ mA}; I_B = 1\text{ mA}$	-	90	110	mV	
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}$	-	115	140	mV	
		$I_C = 1\text{ A}; I_B = 100\text{ mA}$	[1]	-	200	250	mV
R_{CEsat}	collector-emitter saturation resistance	$I_C = 1\text{ A}; I_B = 100\text{ mA}$	[1]	-	200	250	$\text{m}\Omega$
t_d	delay time	$I_C = 0.5\text{ A}; I_{Bon} = 25\text{ mA}; I_{Boff} = -25\text{ mA}$	-	11	-	ns	
t_r	rise time		-	78	-	ns	
t_{on}	turn-on time		-	90	-	ns	
t_s	storage time		-	340	-	ns	
t_f	fall time		-	160	-	ns	
t_{off}	turn-off time		-	500	-	ns	
f_T	transition frequency	$V_{CE} = 10\text{ V}; I_C = 50\text{ mA}; f = 100\text{ MHz}$	150	220	-	MHz	
C_c	collector capacitance	$V_{CB} = 10\text{ V}; I_E = I_e = 0\text{ A}; f = 1\text{ MHz}$	-	5.5	10	pF	
TR2 (PNP)							
h_{FE}	DC current gain	$V_{CE} = -5\text{ V}; I_C = -1\text{ mA}$	200	350	-		
		$V_{CE} = -5\text{ V}; I_C = -500\text{ mA}$	[1]	150	250	-	
		$V_{CE} = -5\text{ V}; I_C = -1\text{ A}$	[1]	100	160	-	

Table 7. Characteristics ...continued
 $T_{amb} = 25\text{ }^{\circ}\text{C}$ unless otherwise specified.

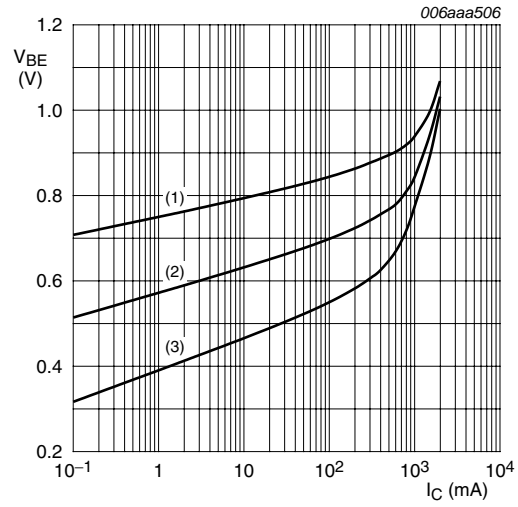
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CEsat}	collector-emitter saturation voltage	$I_C = -100\text{ mA};$ $I_B = -1\text{ mA}$	-	-110	-165	mV
		$I_C = -500\text{ mA};$ $I_B = -50\text{ mA}$	-	-120	-175	mV
		$I_C = -1\text{ A}; I_B = -100\text{ mA}$ [1]	-	-250	-330	mV
R_{CEsat}	collector-emitter saturation resistance	$I_C = -1\text{ A}; I_B = -100\text{ mA}$ [1]	-	250	330	$\text{m}\Omega$
t_d	delay time	$I_C = -0.5\text{ A};$ $I_{Bon} = -25\text{ mA};$ $I_{Boff} = 25\text{ mA}$	-	11	-	ns
t_r	rise time		-	30	-	ns
t_{on}	turn-on time		-	41	-	ns
t_s	storage time		-	205	-	ns
t_f	fall time		-	55	-	ns
t_{off}	turn-off time		-	260	-	ns
f_T	transition frequency		$V_{CE} = -10\text{ V};$ $I_C = -50\text{ mA};$ $f = 100\text{ MHz}$	150	185	-
C_c	collector capacitance	$V_{CB} = -10\text{ V};$ $I_E = I_E = 0\text{ A}; f = 1\text{ MHz}$	-	9	15	pF

[1] Pulse test: $t_p \leq 300\text{ }\mu\text{s}; \delta \leq 0.02$.



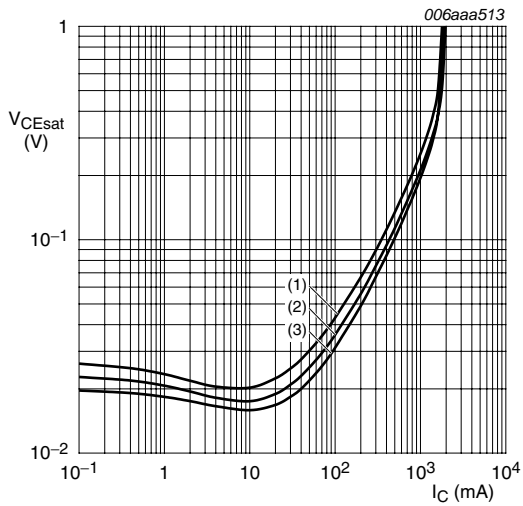
$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = 100\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = -55\text{ }^\circ\text{C}$

Fig 5. TR1 (NPN): DC current gain as a function of collector current; typical values



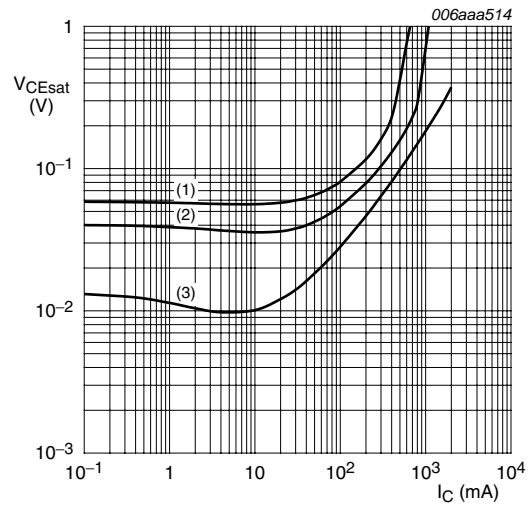
$V_{CE} = 5\text{ V}$
 (1) $T_{amb} = -55\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = 100\text{ }^\circ\text{C}$

Fig 6. TR1 (NPN): Base-emitter voltage as a function of collector current; typical values



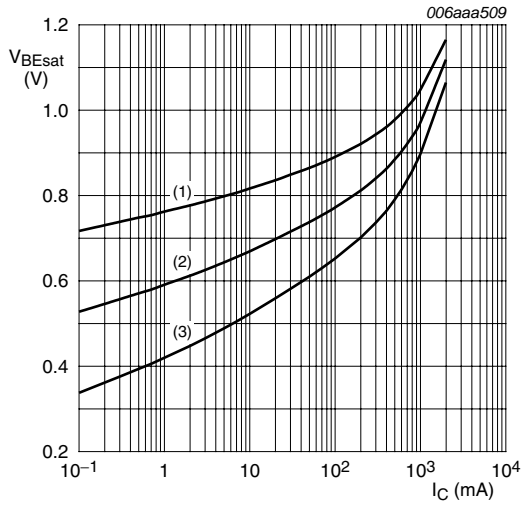
$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = -55\text{ }^\circ\text{C}$

Fig 7. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



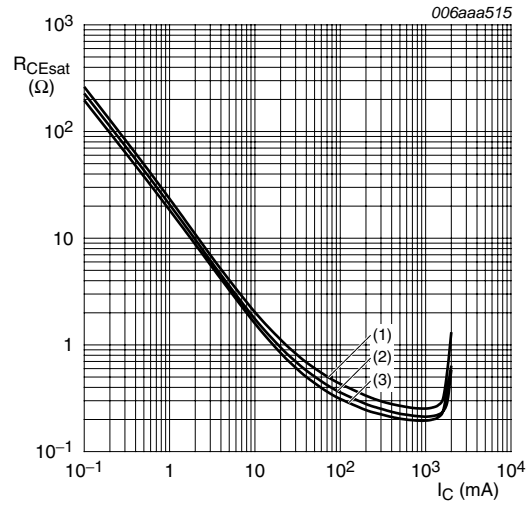
$T_{amb} = 25\text{ }^\circ\text{C}$
 (1) $I_C/I_B = 100$
 (2) $I_C/I_B = 50$
 (3) $I_C/I_B = 10$

Fig 8. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



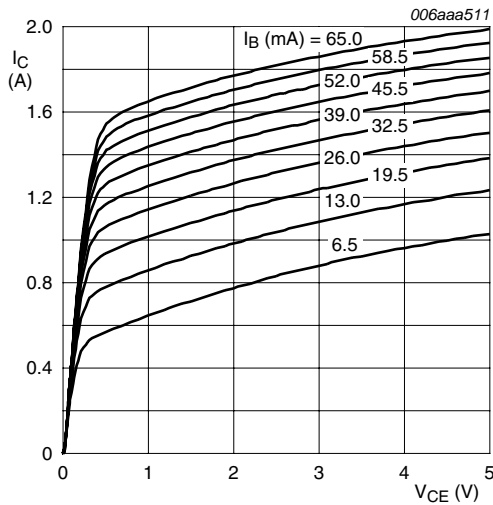
- $I_C/I_B = 20$
- (1) $T_{amb} = -55^\circ C$
 - (2) $T_{amb} = 25^\circ C$
 - (3) $T_{amb} = 100^\circ C$

Fig 9. TR1 (NPN): Base-emitter saturation voltage as a function of collector current; typical values



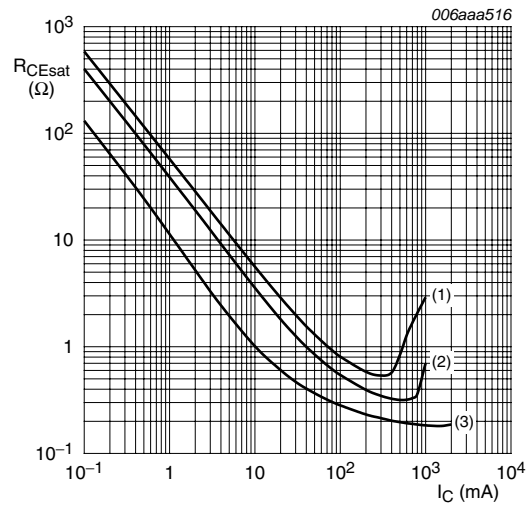
- $I_C/I_B = 20$
- (1) $T_{amb} = 100^\circ C$
 - (2) $T_{amb} = 25^\circ C$
 - (3) $T_{amb} = -55^\circ C$

Fig 10. TR1 (NPN): Collector-emitter saturation resistance as a function of collector current; typical values



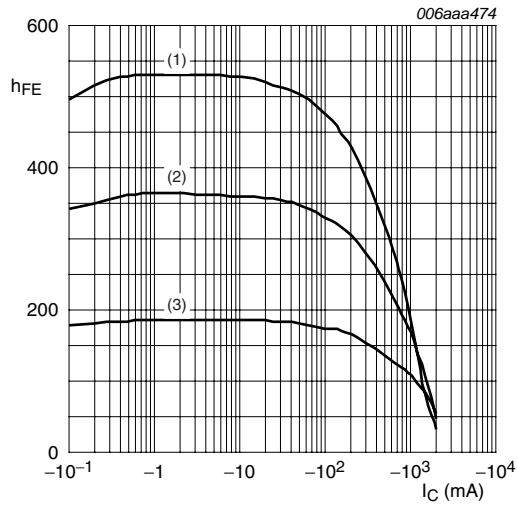
$T_{amb} = 25^\circ C$

Fig 11. TR1 (NPN): Collector current as a function of collector-emitter voltage; typical values



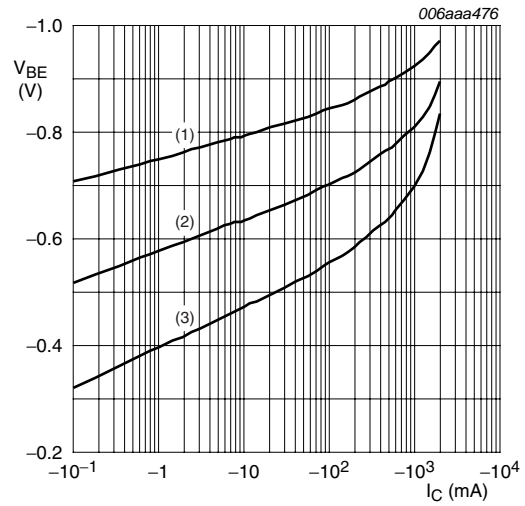
- $T_{amb} = 25^\circ C$
- (1) $I_C/I_B = 100$
 - (2) $I_C/I_B = 50$
 - (3) $I_C/I_B = 10$

Fig 12. TR1 (NPN): Collector-emitter saturation resistance as a function of collector current; typical values



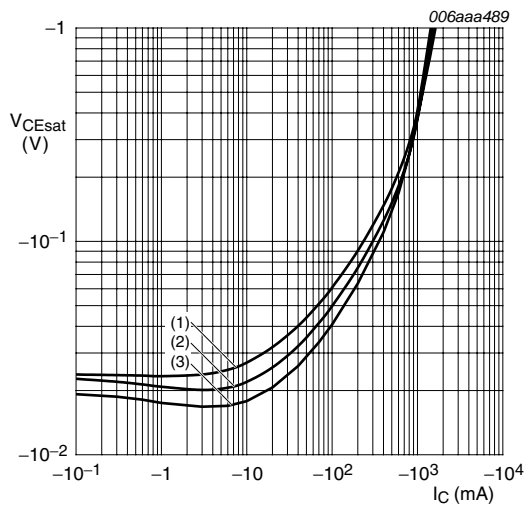
$V_{CE} = -5\text{ V}$
 (1) $T_{amb} = 100\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = -55\text{ }^\circ\text{C}$

Fig 13. TR2 (PNP): DC current gain as a function of collector current; typical values



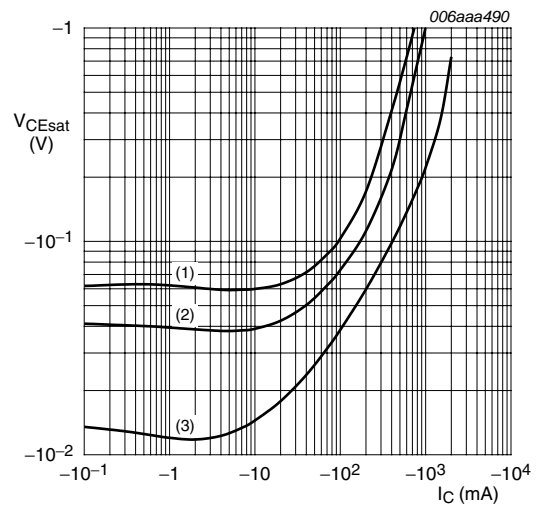
$V_{CE} = -5\text{ V}$
 (1) $T_{amb} = -55\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = 100\text{ }^\circ\text{C}$

Fig 14. TR2 (PNP): Base-emitter voltage as a function of collector current; typical values



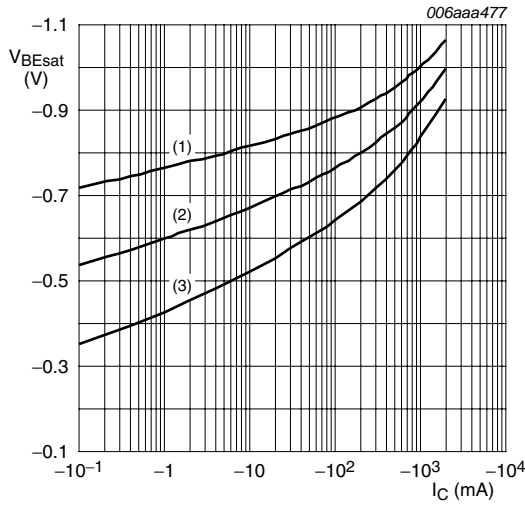
$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ }^\circ\text{C}$
 (2) $T_{amb} = 25\text{ }^\circ\text{C}$
 (3) $T_{amb} = -55\text{ }^\circ\text{C}$

Fig 15. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values



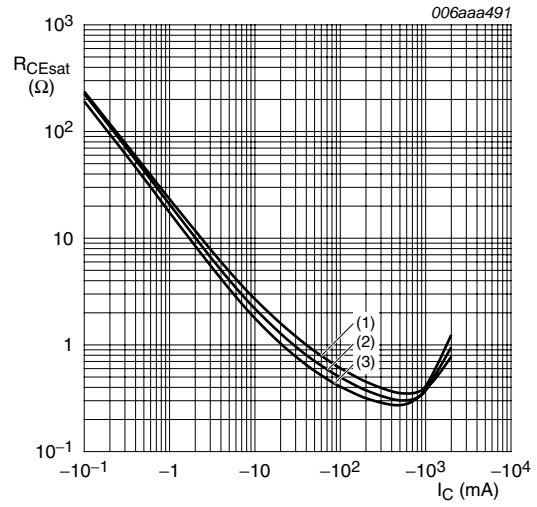
$T_{amb} = 25\text{ }^\circ\text{C}$
 (1) $I_C/I_B = 100$
 (2) $I_C/I_B = 50$
 (3) $I_C/I_B = 10$

Fig 16. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values



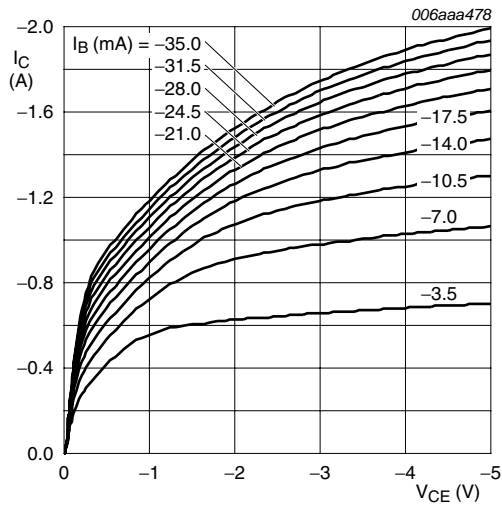
$I_C/I_B = 20$
 (1) $T_{amb} = -55\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 100\text{ °C}$

Fig 17. TR2 (PNP): Base-emitter saturation voltage as a function of collector current; typical values



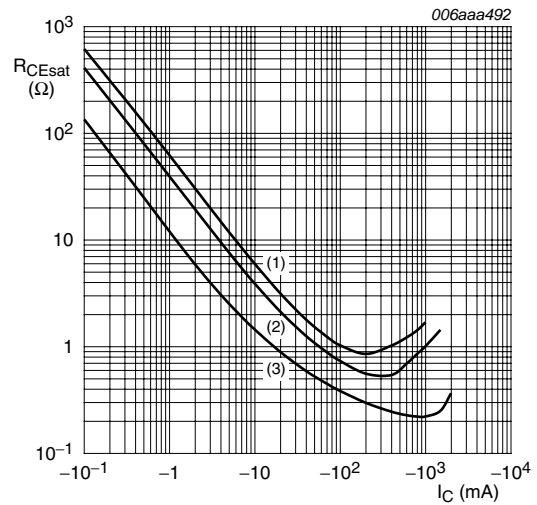
$I_C/I_B = 20$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig 18. TR2 (PNP): Collector-emitter saturation resistance as a function of collector current; typical values



$T_{amb} = 25\text{ °C}$

Fig 19. TR2 (PNP): Collector current as a function of collector-emitter voltage; typical values



$T_{amb} = 25\text{ °C}$
 (1) $I_C/I_B = 100$
 (2) $I_C/I_B = 50$
 (3) $I_C/I_B = 10$

Fig 20. TR2 (PNP): Collector-emitter saturation resistance as a function of collector current; typical values

8. Test information

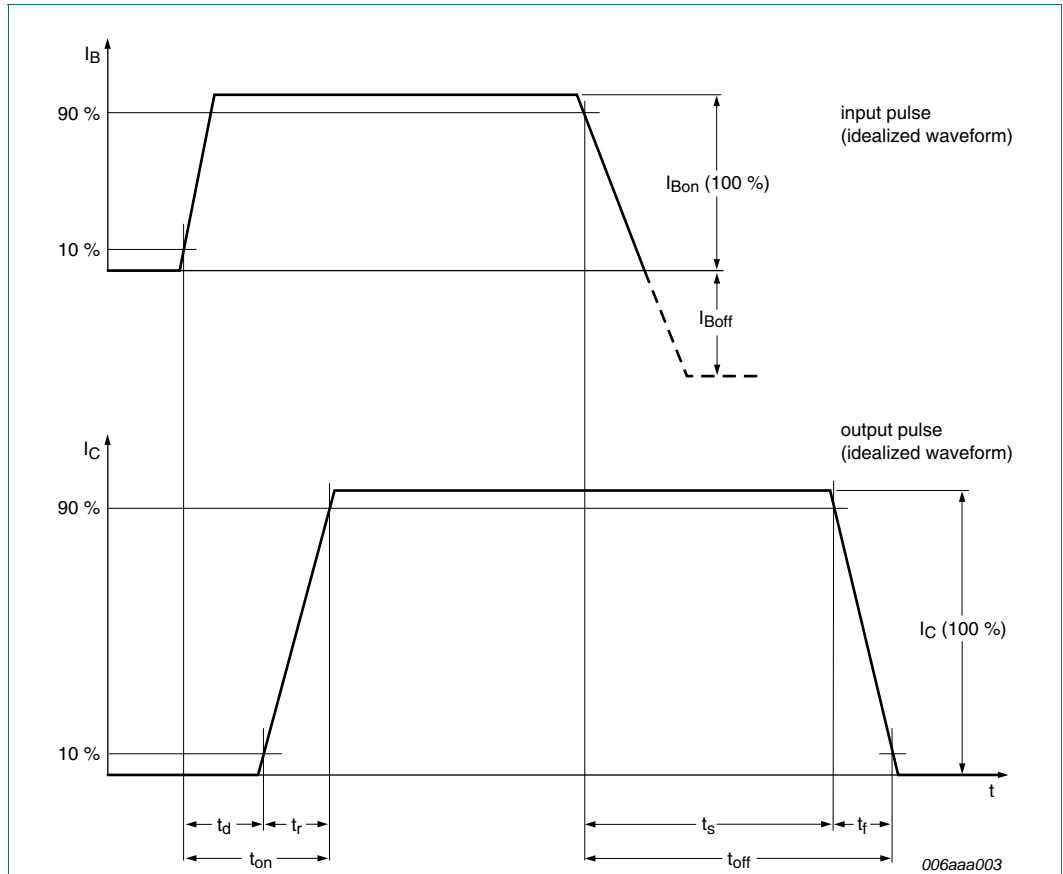
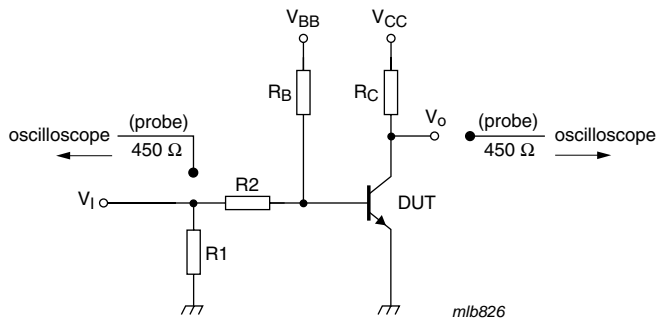


Fig 21. TR1 (NPN): BISS transistor switching time definition



$I_C = 0.5 \text{ A}$; $I_{B_{on}} = 25 \text{ mA}$; $I_{B_{off}} = -25 \text{ mA}$; $R_1 = \text{open}$; $R_2 = 100 \text{ } \Omega$; $R_B = 300 \text{ } \Omega$; $R_C = 20 \text{ } \Omega$

Fig 22. TR1 (NPN): Test circuit for switching times

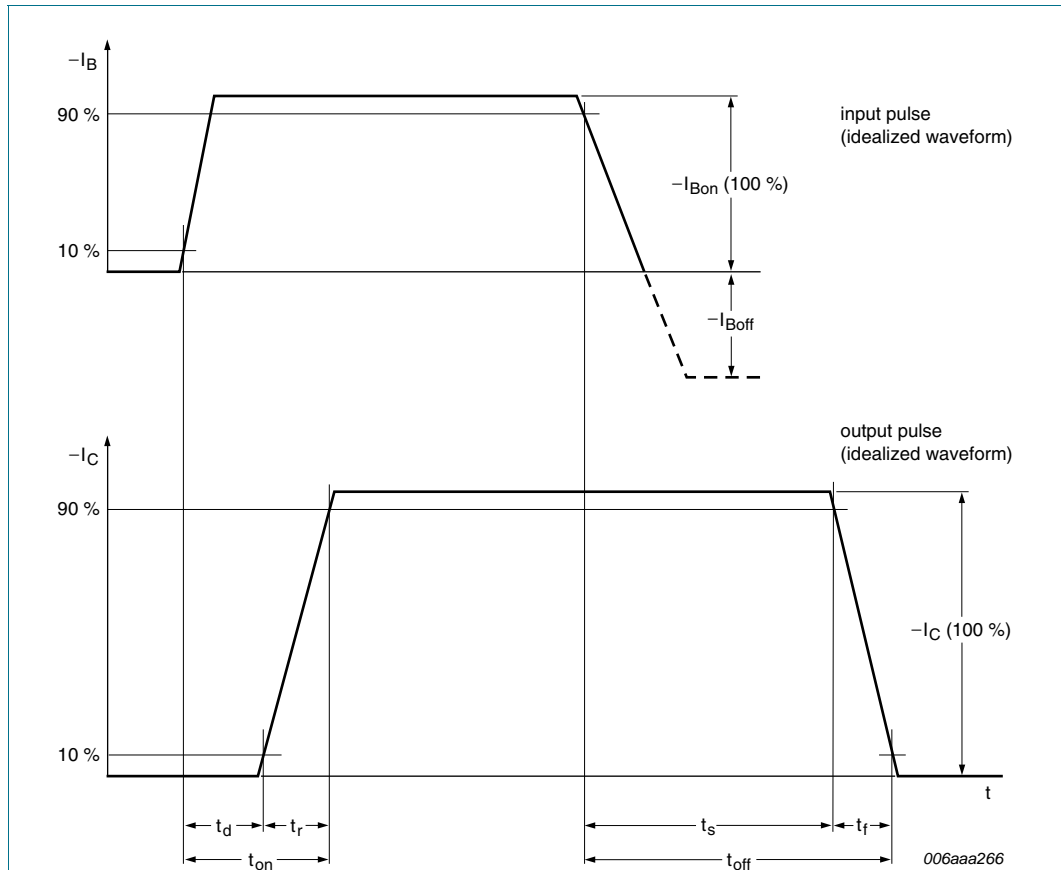
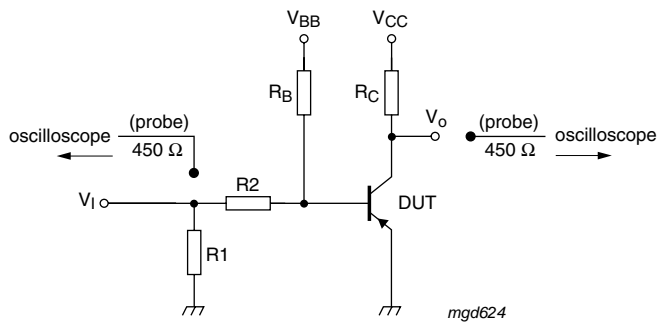


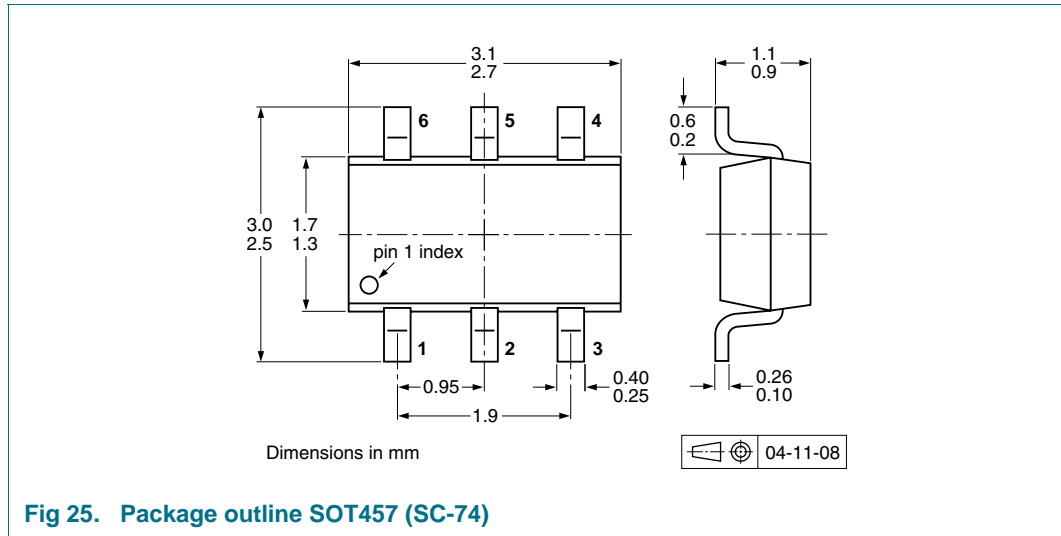
Fig 23. TR2 (PNP): BISS transistor switching time definition



$I_C = -0.5 \text{ A}$; $I_{Bon} = -25 \text{ mA}$; $I_{Boff} = 25 \text{ mA}$; $R_1 = \text{open}$; $R_2 = 100 \Omega$; $R_B = 300 \Omega$; $R_C = 20 \Omega$

Fig 24. TR2 (PNP): Test circuit for switching times

9. Package outline



10. Packing information

Table 8. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

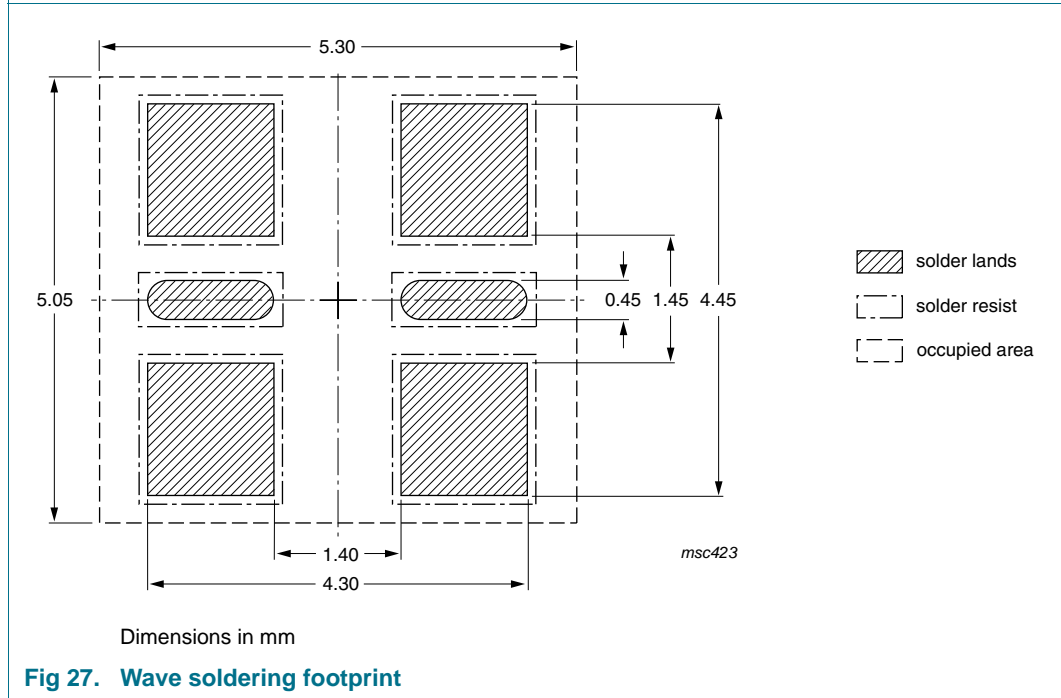
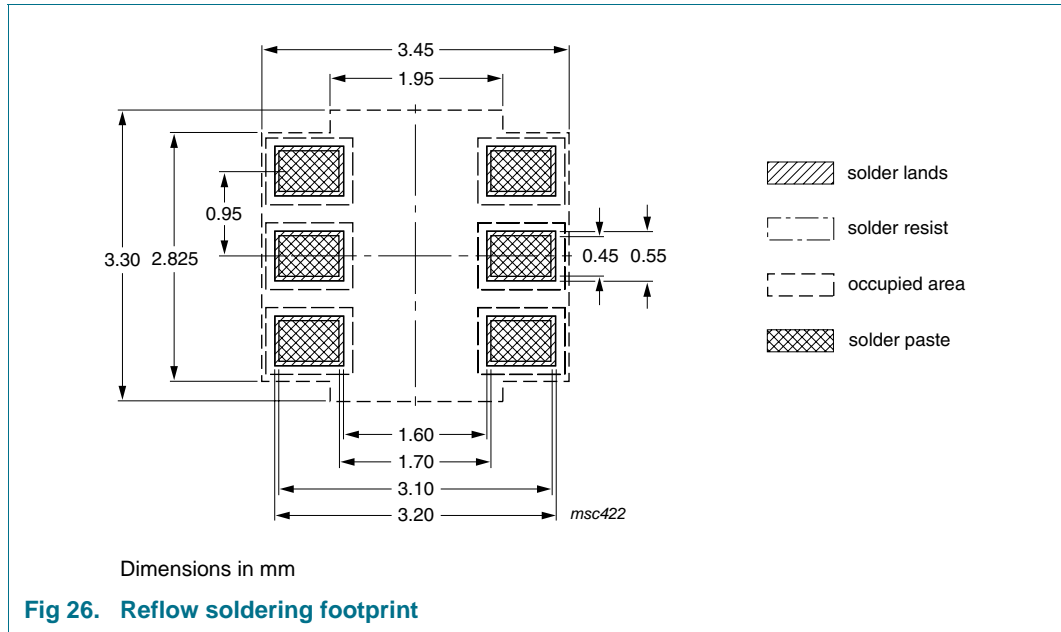
Type number	Package	Description	Packing quantity	
			3000	10000
PBSS4160DPN	SOT457	4 mm pitch, 8 mm tape and reel; T1 ^[2]	-115	-135
		4 mm pitch, 8 mm tape and reel; T2 ^[3]	-125	-165

[1] For further information and the availability of packing methods, see [Section 14](#).

[2] T1: normal taping

[3] T2: reverse taping

11. Soldering



12. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4160DPN_3	20091211	Product data sheet	-	PBSS4160DPN_2
Modifications:	<ul style="list-style-type: none"> This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content. Figure 1, 7 and 15: updated 			
PBSS4160DPN_2	20050714	Product data sheet	-	PBSS4160DPN_1
PBSS4160DPN_1	20040603	Objective data sheet	-	-

13. Legal information

13.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

13.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

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